Abstract of the Disclosure

The present invention enhances silicon etching rate and improves the productivity of a silicon etching apparatus. Chlorine gas is supplied at 250 ml/min or above, oxygen gas is added to the chlorine gas in 2.0 % by volume or below of the chlorine gas, the workpiece is maintained at 0°C or below or the stage mounted with the workpiece is maintained at -10°C or below during etching.

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